



SEOUL SEMICONDUCTOR

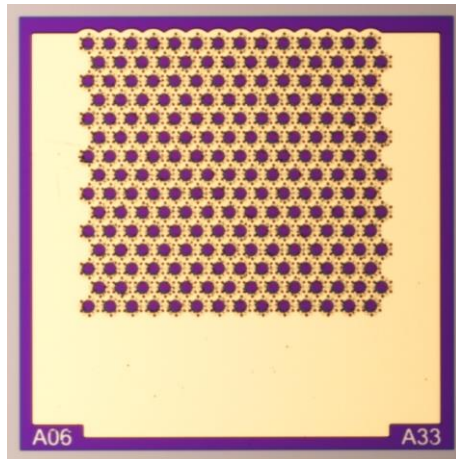
RS850-MI200

Data Sheet

EF개발 4담당

1. Chip dimensions

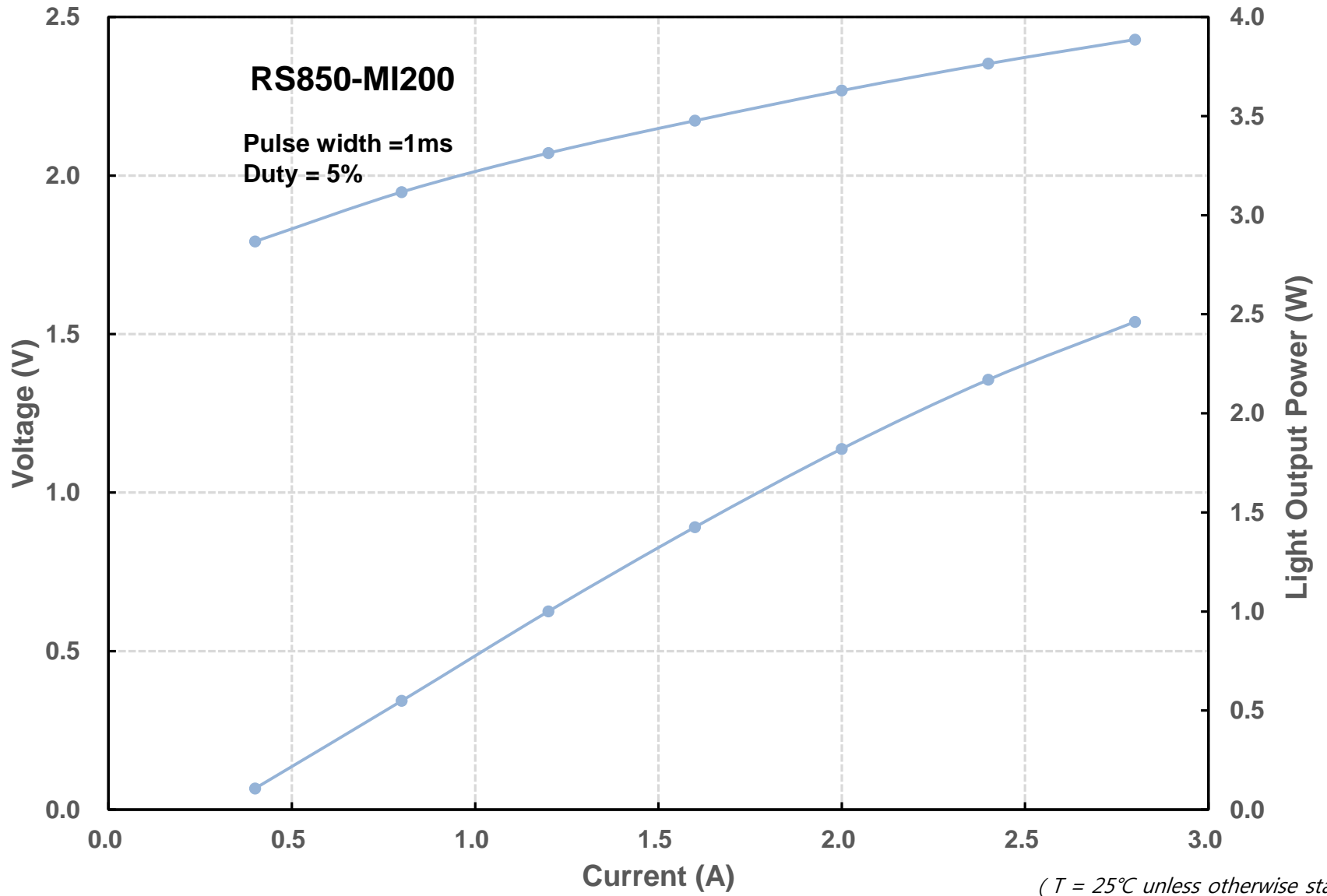
Unit : 705 μm x 705 μm
Chip : top side view



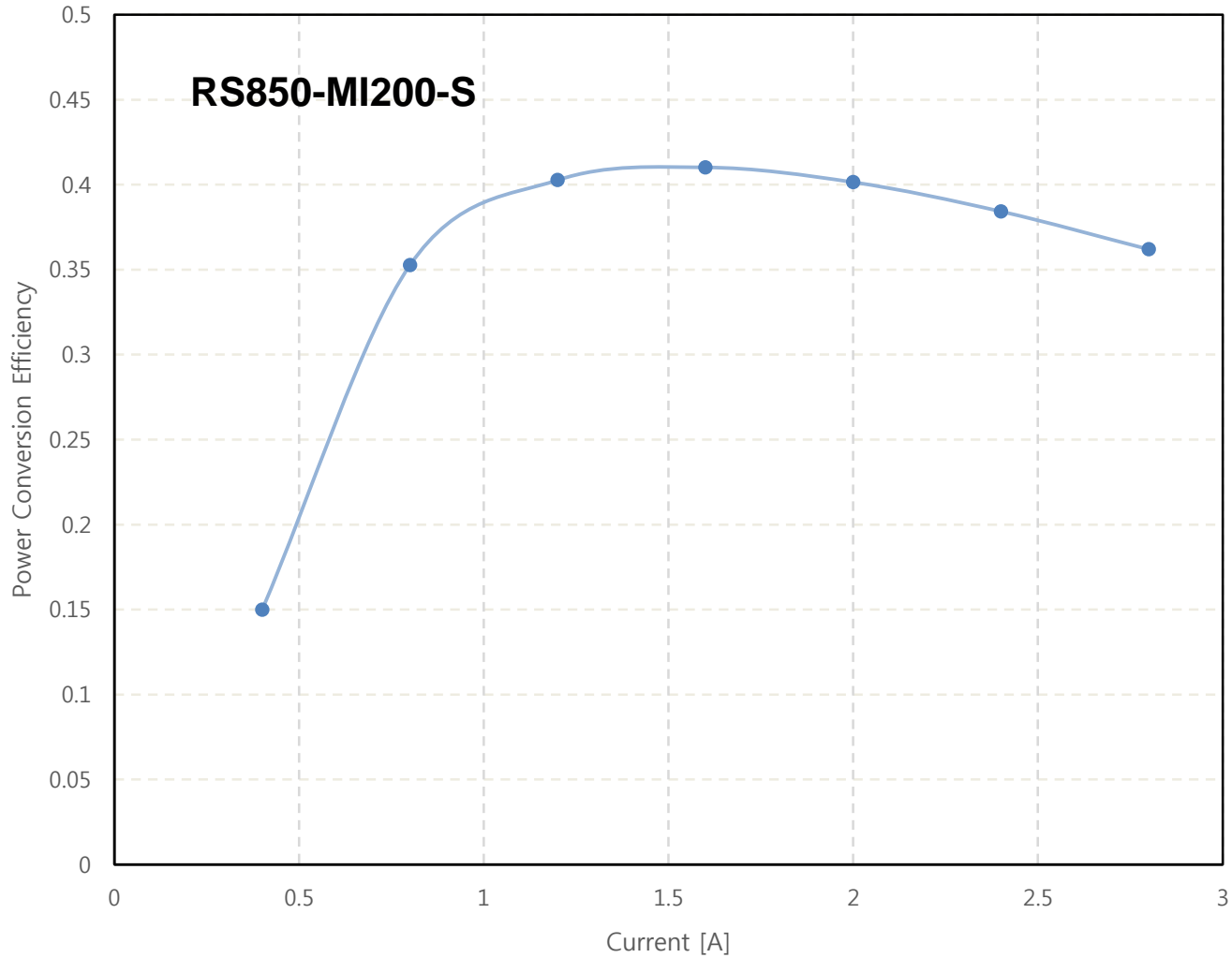
Cathode : backside

Thickness : 150 \pm 20 μm

2. L-I-V (25°C)

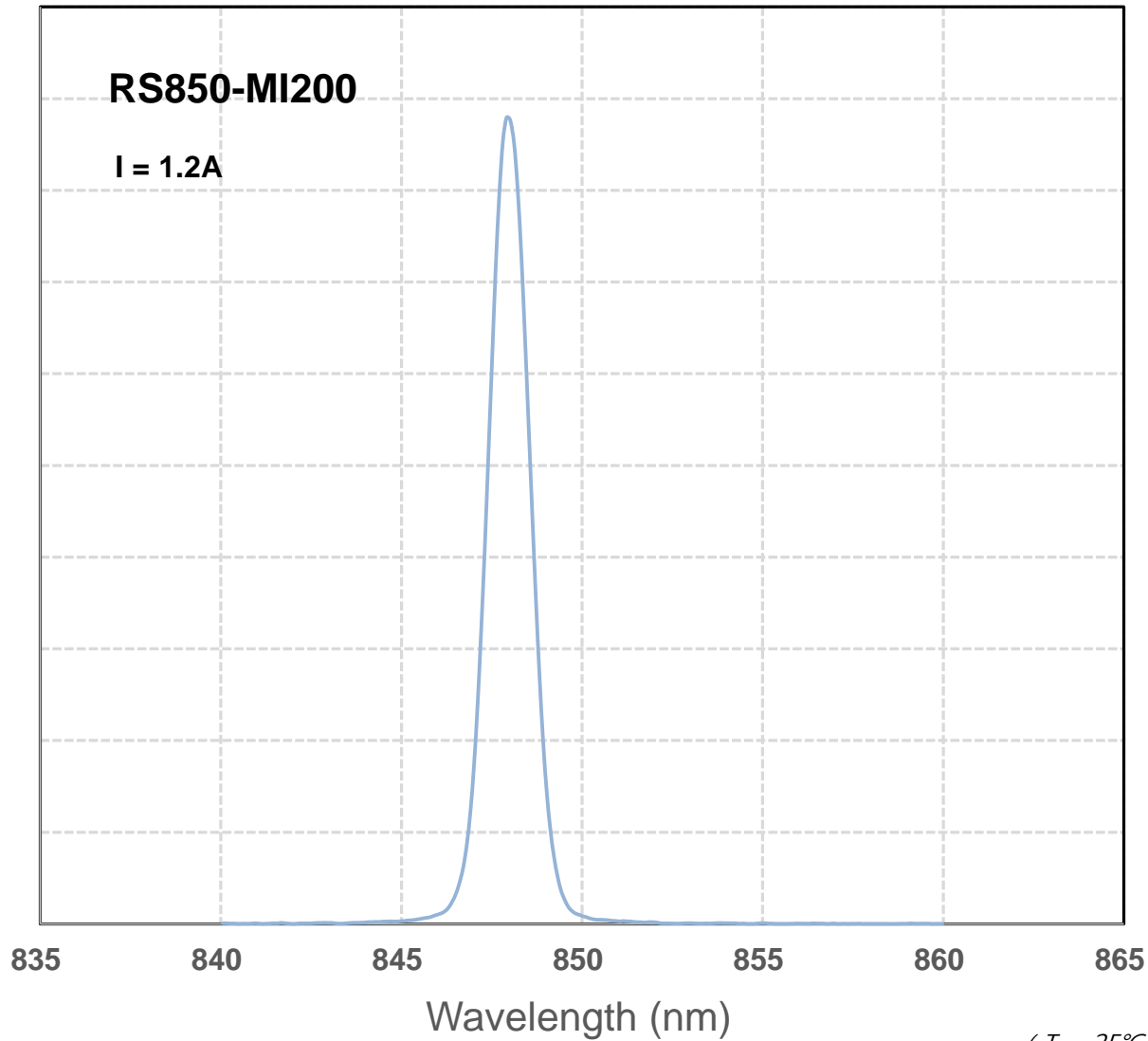


3. WPE vs Current (25°C)



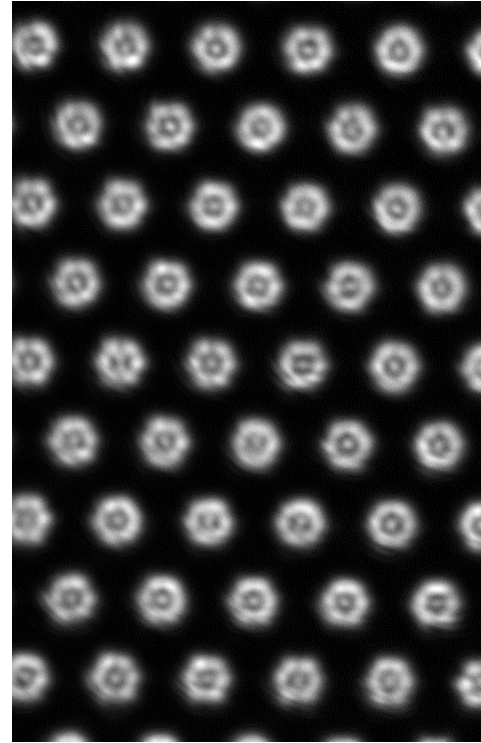
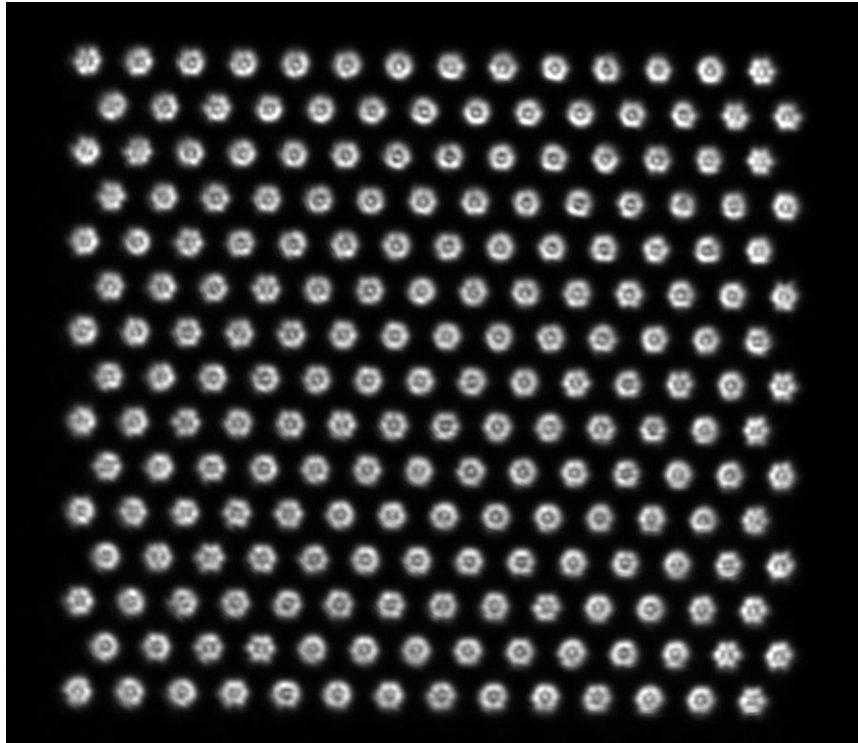
(T = 25°C unless otherwise stated)

4. Spectrum vs Current (25°C)



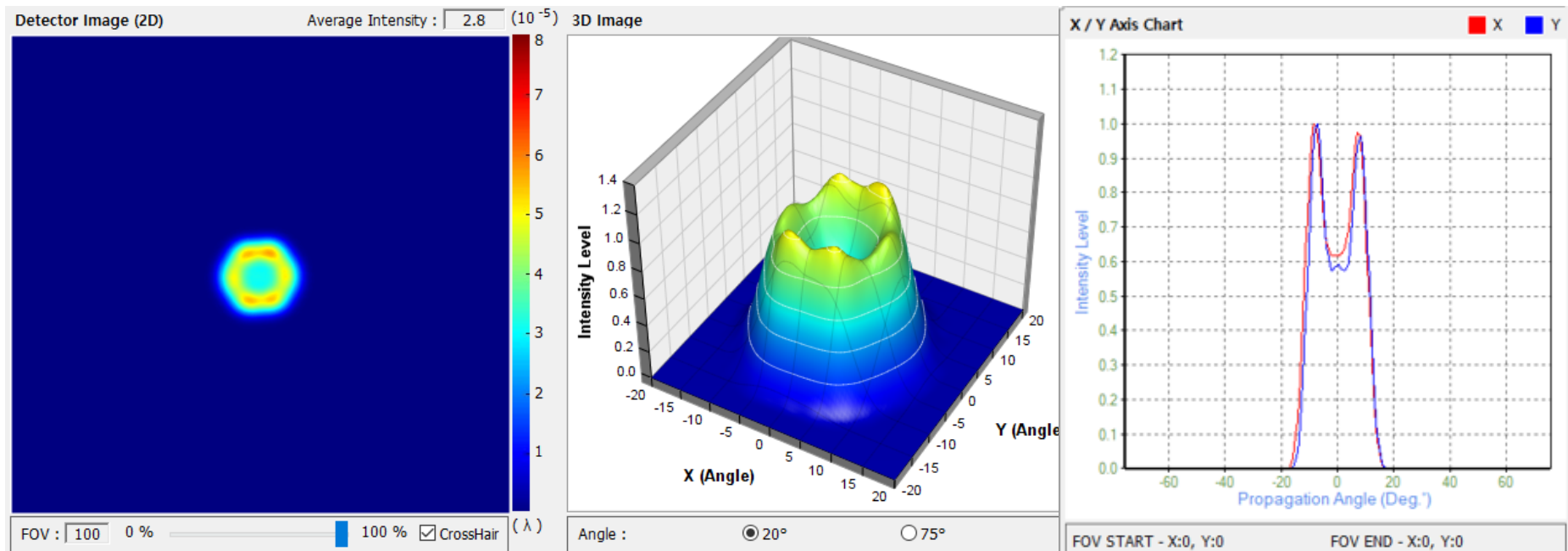
(T = 25°C unless otherwise stated)

5. Near-field vs Current (25°C)



($T = 25^{\circ}\text{C}$ unless otherwise stated)

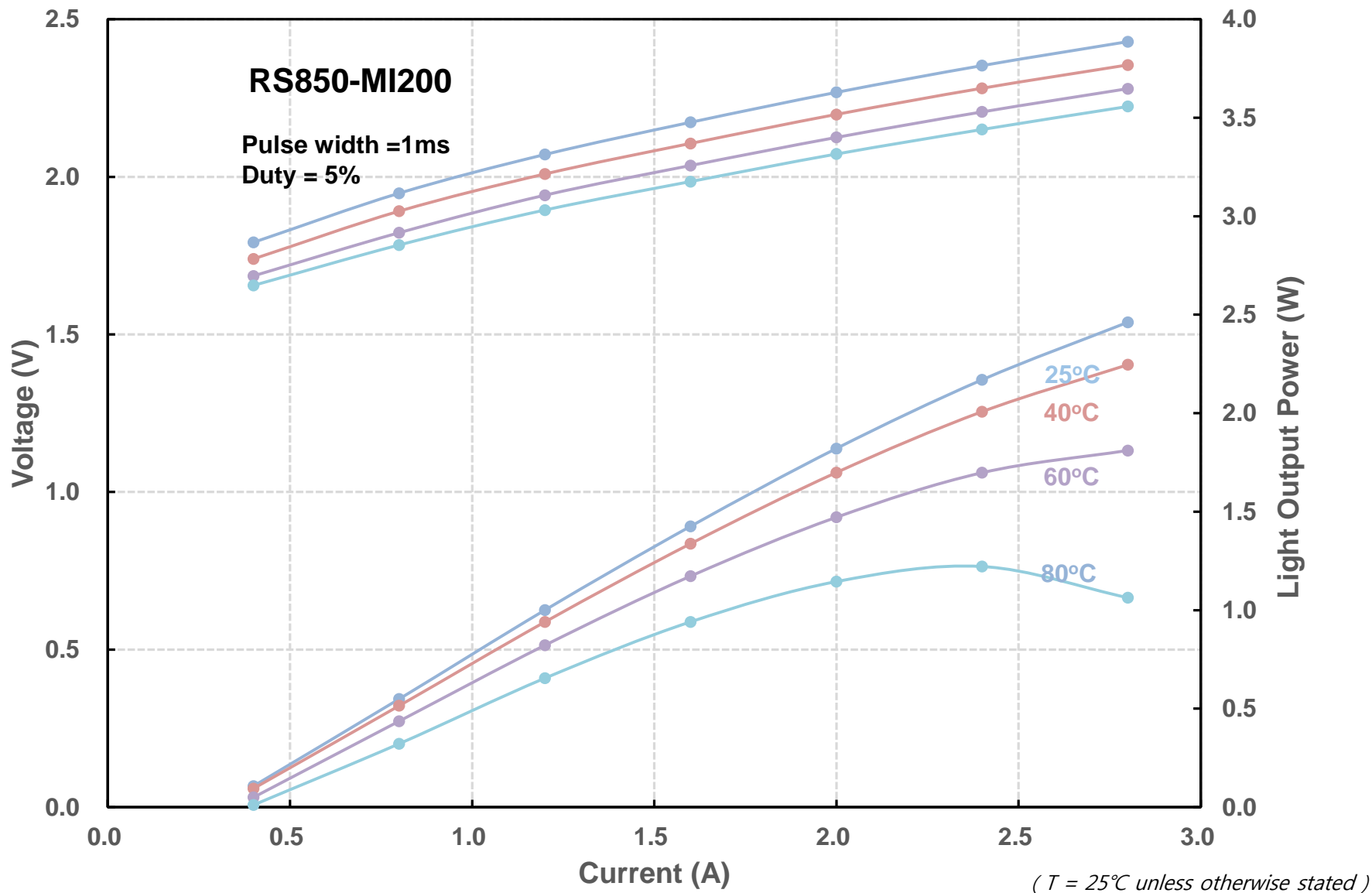
6. Far-field vs Current (25°C)



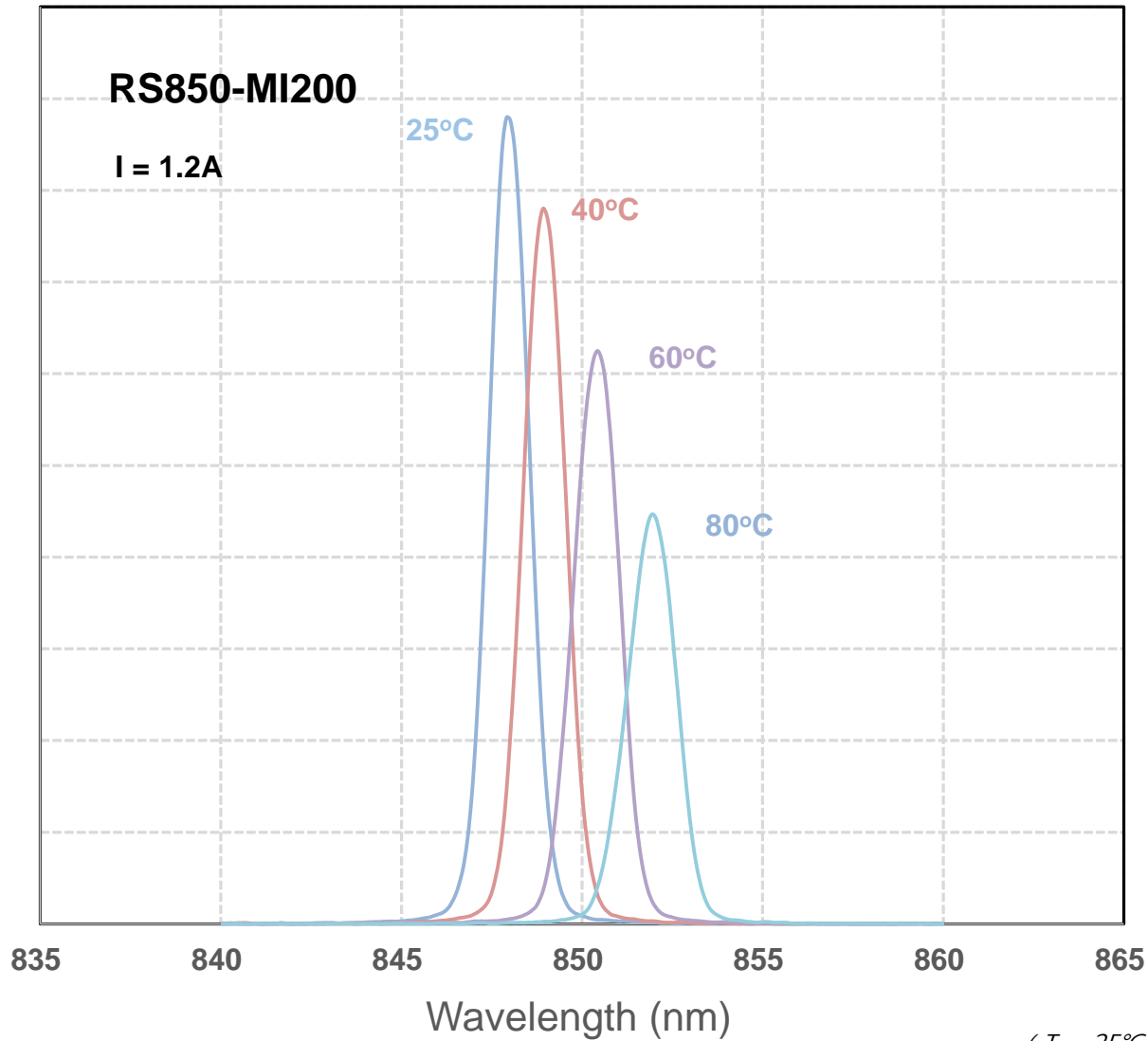
	Current (A)	Pulse 조건(s) (on time/off time)	Shutter Speed (μs)	FWHM (°)	1/e ² (°)	Peak to Peak angle (°)	FOI angle (°)	Peak 1 intensity	Peak 2 intensity	Center intensity
Phi=0 (x-axis)	1.200	0.001/0.0323333	1000	23.0	28.0	15.5	150.8	1.0	1.0	0.6
Phi= 90 (y-axis)	1.200	0.001/0.0323333	1000	22.5	27.0	15.5	150.8	1.0	1.0	0.6

(T = 25°C unless otherwise stated)

7. L-I-V vs Temperature



8. Spectrum vs Temperature



(T = 25°C unless otherwise stated)



THANK YOU!

www.seoulsemicon.com